RAYCONN ELECTRONICS CO., LTD.

SPECIFICATION FORM

FEATURES

- ✧ 0.56 INCHES (14.20MM) DIGIT HEIGHT
- ✧ 37.60MM×19.00MM OUTLINE
- ✧ THREE DIGIT
- ✧ MONO COLOR
- ✧ EASY ASSEMBLY
- ✧ HIGH BRIGHTNESS
- ✧ SOLID STATE RELIABILITY

DESCRIPTION

The REC-S5361CG/AG is a 0.56 inches (14.20mm) digit height, 37.60mm×19.0mm outline, single color, three digits numeric display. This display utilizes green LED chips fabricated from GaP epiwafer on GaP substrate grown by liquid phase epitaxy.. These devices have black face and white segments.

DEVICE

PART NO.	EMITTING COLOR	DESCRIPTION
RECS5361CG/AG	Yellow-Green	Common Cathode,Black Face & White Seg.

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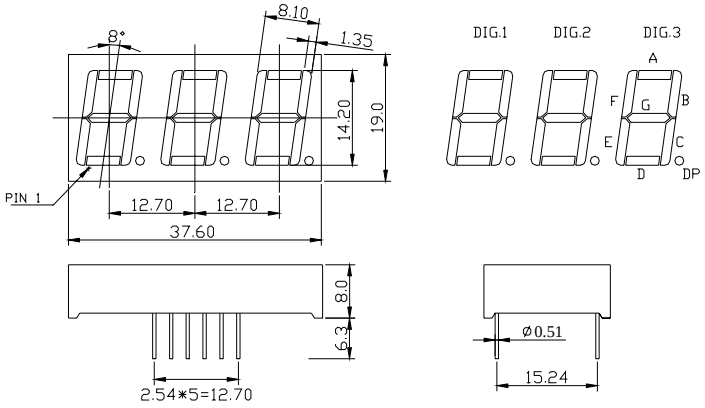
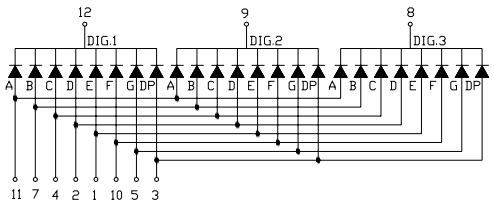
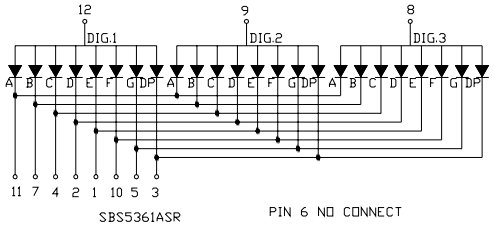
PACKAGE DIMENSION



Notes: 1.All dimension are in millimeters.
2.Tolerance is ± 0.25mm unless otherwise specified.

INTERNAL CIRCUIT DIAGRAM





PIN CONNECTION

PIN NO.	CONNECTION		PIN NO.	CONNECTION	
	SBS5361CSR	SBS5361ASR		SBS5361CSR	SBS5361ASR
1	Anode E	Cathode E	7	Anode B	Cathode E
2	Anode D	Cathode D	8	Cathode Dig. 3	Anode Dig. 3
3	Anode DP	Cathode DP	9	Cathode Dig. 2	Anode Dig. 2
4	Anode C	Cathode C	10	Anode F	Cathode F
5	Anode G	Cathode G	11	Anode A	Cathode A
6	No Connect	No Connect	12	Cathode Dig. 1	Anode Dig. 1

ABSOLUTE MAXIMUM RATING AT T_A=25°C

PARAMETER	SYMBOL	MAXIMUM	UNIT
Power Dissipation per Seg.	P_{AD}	75	mW
Peak Forward Current per Seg.	I_{PF}	80	mA
Continuous Forward Current per Seg.	I_{AF}	20	mA
Reverse Voltage per Seg.	V_R	5	V
Operating Temperature Range, T_{opr}	- 25°C to + 60°C		
Storage Temperature Range, T_{stg}	- 30°C to + 85°C		
Solder Temperature : 1 / 16 inch below seating plane for 3 seconds at 260°C			

ELECTRO – OPTICAL CHARACTERISTICS AT T_A=25°C

PARAMETER	UNIT	MIN	TYPE	MAX
Luminous Intensity per Seg., I_V (I_F=20mA)	mcd	7	10	12
Peak Emission Wavelength, λ_P (I_F=20mA)	nm		570	
Special Line Half-Width, $\Delta\lambda$ (I_F=20mA)	nm		20	
Forward Voltage per Seg., V_F (I_F=20mA)	V	1.6	1.8	2.1
Reverse Current per chipSeg., I_R, (V_R=5V)	μA			100
Luminous Intensity Matching Ratio, $I_{V\text{-}m}$ (I_F=20mA)				2:1